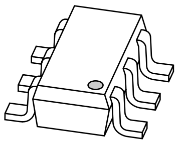


PBSS5160DS

60 V, 1 A PNP low V_{CEsat} (BISS) transistor

Rev. 02 — 28 June 2005 Product data sheet

1. Product profile

1.1 General description

PNP/PNP low V_{CEsat} Breakthrough in Small Signal (BISS) transistor pair in a SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

NPN complement: PBSS4160DS.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Dual low power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1: Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	–60	V
I_C	collector current (DC)		[1]	-	-	–1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	-	–2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1$ A; $I_B = -100$ mA	[2]	-	250	330	mΩ

[1] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.

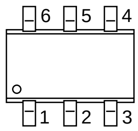
[2] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.

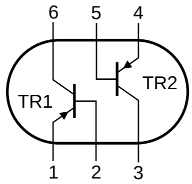
PHILIPS

2. Pinning information

Table 2: Pinning

Pin	Description	Simplified outline	Symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		





sym018

3. Ordering information

Table 3: Ordering information

Type number	Package		
	Name	Description	Version
PBSS5160DS	SC-74	plastic surface mounted package; 6 leads	SOT457

4. Marking

Table 4: Marking codes

Type number	Marking code
PBSS5160DS	A5

5. Limiting values

Table 5: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V_{CBO}	collector-base voltage	open emitter		-	–80	V
V_{CEO}	collector-emitter voltage	open base		-	–60	V
V_{EBO}	emitter-base voltage	open collector		-	–5	V
I_C	collector current (DC)		[1]	-	–0.77	A
			[2]	-	–0.9	A
			[3]	-	–1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	–2	A
I_B	base current (DC)			-	–300	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms		-	–1	A

Table 5: Limiting values *…continued*

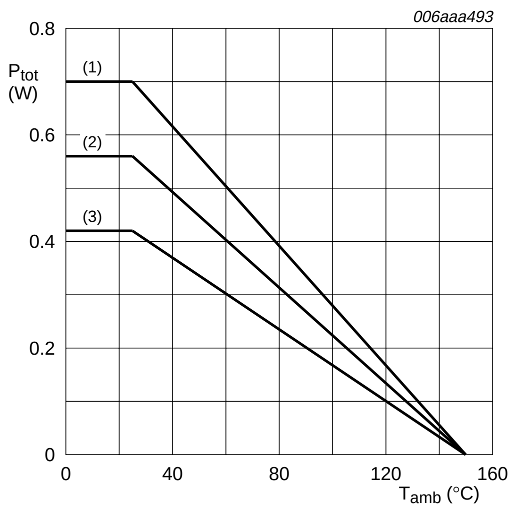
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	290	mW
			[2]	-	370	mW
			[3]	-	450	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	420	mW
			[2]	-	560	mW
			[3]	-	700	mW
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			–65	+150	°C
T_{stg}	storage temperature			–65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[3] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.



(1) Ceramic PCB, Al_2O_3, standard footprint

(2) FR4 PCB, mounting pad for collector 1 cm^2

(3) FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

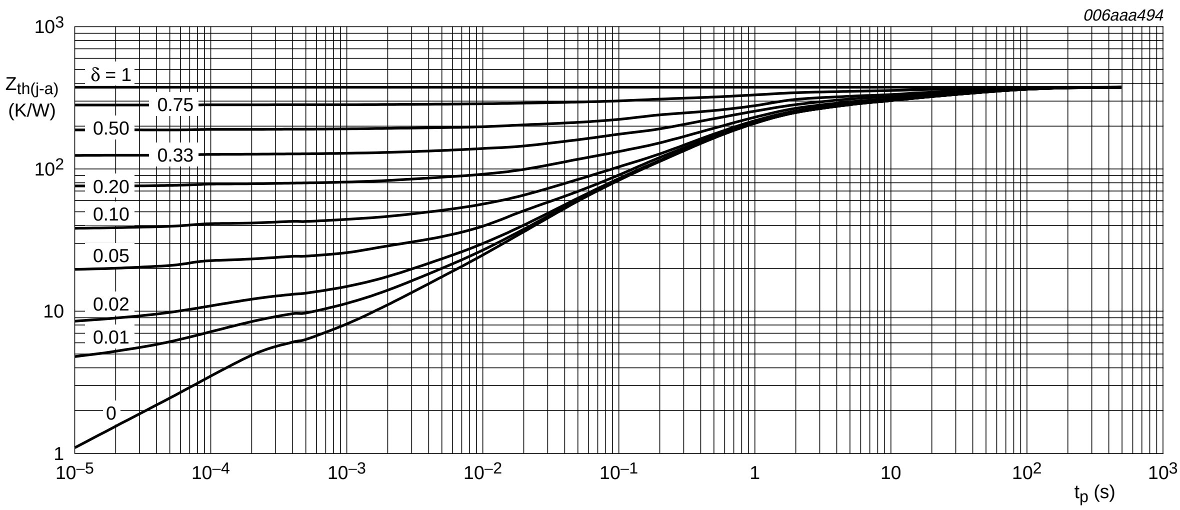
Table 6: Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	431	K/W
			[2]	-	-	338	K/W
			[3]	-	-	278	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	298	K/W
			[2]	-	-	223	K/W
			[3]	-	-	179	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

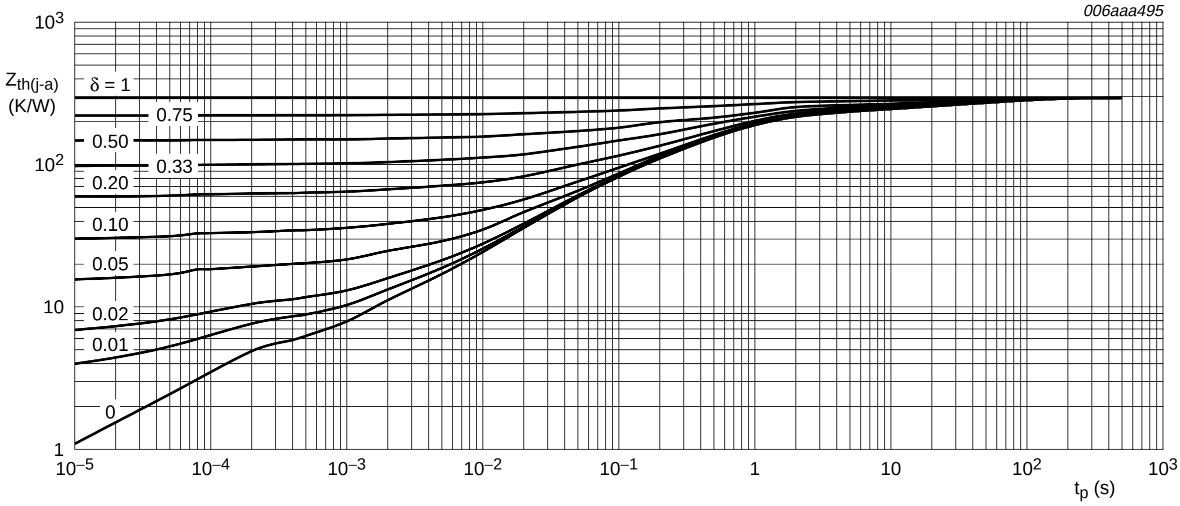
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm^2.

[3] Device mounted on a ceramic PCB, Al_2O_3, standard footprint.



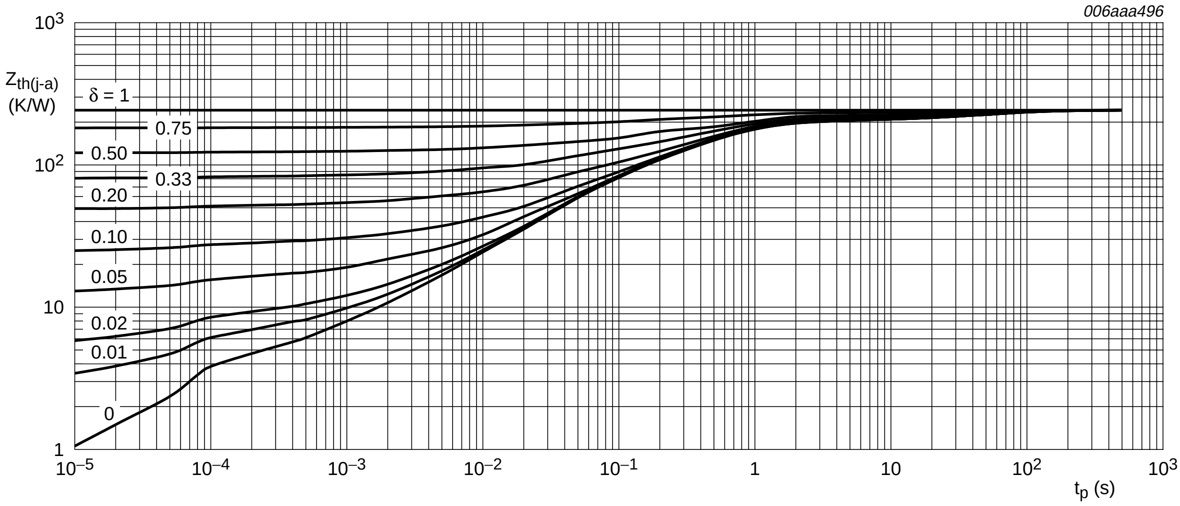
FR4 PCB, standard footprint

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



FR4 PCB, mounting pad for collector 1 cm^2

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values



Ceramic PCB, Al_2O_3, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

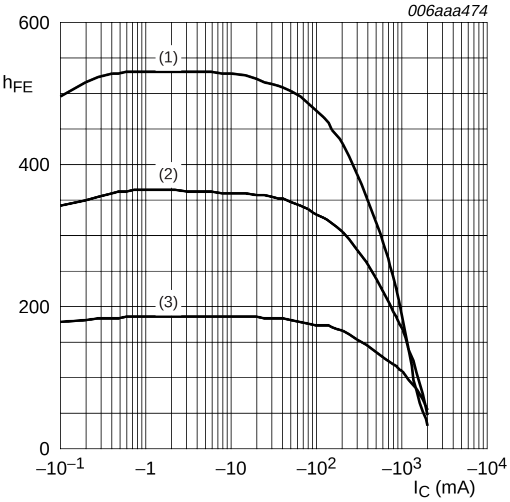
7. Characteristics

Table 7: Characteristics

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
I_{CBO}	collector-base cut-off current	V_{CB} = –60 V; I_E = 0 A		-	-	–100	nA
		V_{CB} = –60 V; I_E = 0 A; T_j = 150 °C		-	-	–50	µA
I_{CES}	collector-emitter cut-off current	V_{CE} = –60 V; V_{BE} = 0 V		-	-	–100	nA
I_{EBO}	emitter-base cut-off current	V_{EB} = –5 V; I_C = 0 A		-	-	–100	nA
h_{FE}	DC current gain	V_{CE} = –5 V; I_C = –1 mA		200	350	-	
		V_{CE} = –5 V; I_C = –500 mA	[1]	150	250	-	
		V_{CE} = –5 V; I_C = –1 A	[1]	100	160	-	
V_{CEsat}	collector-emitter saturation voltage	I_C = –100 mA; I_B = –1 mA		-	–110	–165	mV
		I_C = –500 mA; I_B = –50 mA		-	–120	–175	mV
		I_C = –1 A; I_B = –100 mA	[1]	-	–250	–330	mV
V_{BEsat}	base-emitter saturation voltage	I_C = –1 A; I_B = –50 mA	[1]	-	–0.95	–1.1	V
R_{CEsat}	collector-emitter saturation resistance	I_C = –1 A; I_B = –100 mA	[1]	-	250	330	mΩ
V_{BEon}	base-emitter turn-on voltage	I_C = –1 A; V_{CE} = –5 V	[1]	-	–0.82	–0.9	V
t_d	delay time	I_C = –0.5 A; I_{Bon} = –25 mA; I_{Boff} = 25 mA		-	11	-	ns
t_r	rise time			-	30	-	ns
t_{on}	turn-on time			-	41	-	ns
t_s	storage time			-	205	-	ns
t_f	fall time			-	55	-	ns
t_{off}	turn-off time			-	260	-	ns
f_T	transition frequency	V_{CE} = –10 V; I_C = –50 mA; f = 100 MHz		150	185	-	MHz
C_c	collector capacitance	V_{CB} = –10 V; I_E = i_e = 0 A; f = 1 MHz		-	9	15	pF

[1] Pulse test: $t_p \leq 300$ µs; $\delta \leq 0.02$.



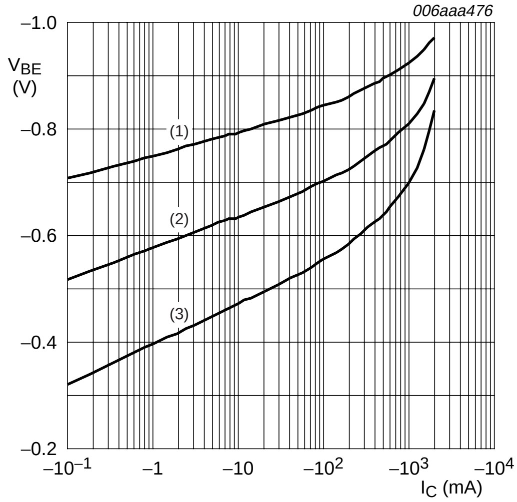
$V_{CE} = -5$ V

(1) $T_{amb} = 100$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 5. DC current gain as a function of collector current; typical values



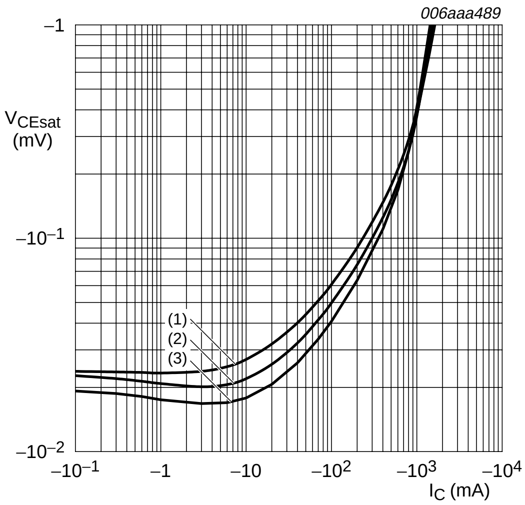
$V_{CE} = -5$ V

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = 100$ °C

Fig 6. Base-emitter voltage as a function of collector current; typical values



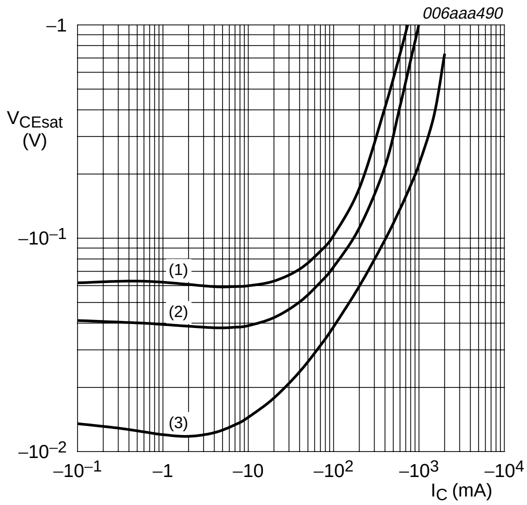
$I_C/I_B = 20$

(1) $T_{amb} = 100$ °C

(2) $T_{amb} = 25$ °C

(3) $T_{amb} = -55$ °C

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values



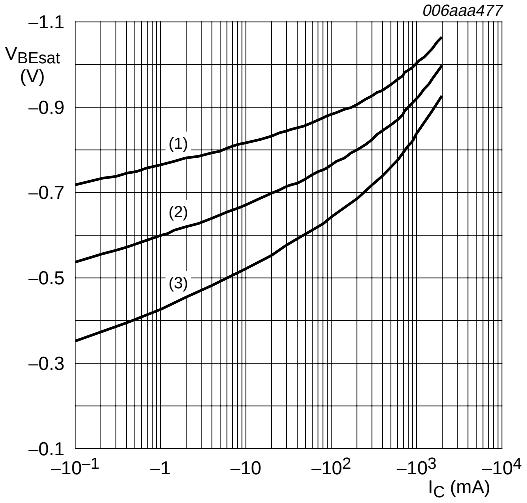
$T_{amb} = 25$ °C

(1) $I_C/I_B = 100$

(2) $I_C/I_B = 50$

(3) $I_C/I_B = 10$

Fig 8. Collector-emitter saturation voltage as a function of collector current; typical values



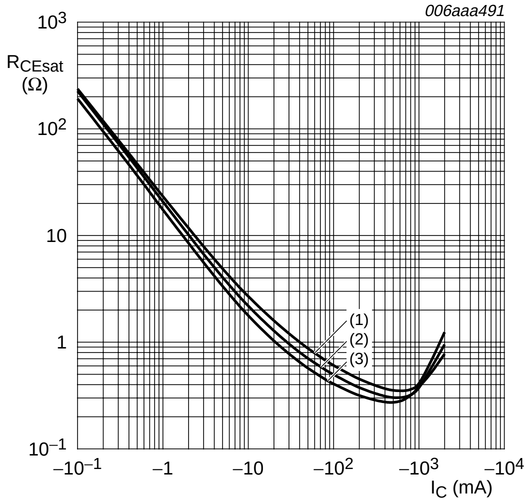
$I_C/I_B = 20$

(1) $T_{amb} = -55\ °C$

(2) $T_{amb} = 25\ °C$

(3) $T_{amb} = 100\ °C$

Fig 9. Base-emitter saturation voltage as a function of collector current; typical values



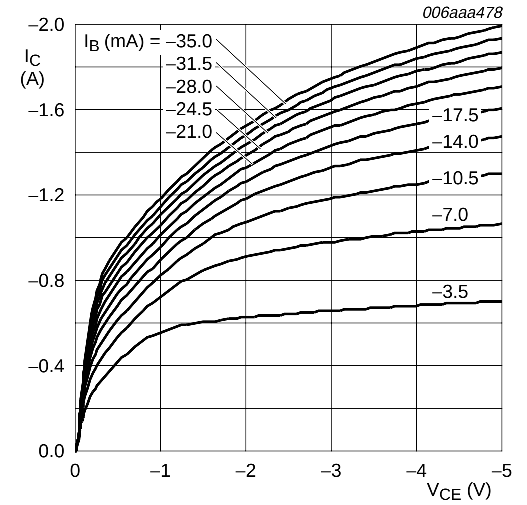
$I_C/I_B = 20$

(1) $T_{amb} = 100\ °C$

(2) $T_{amb} = 25\ °C$

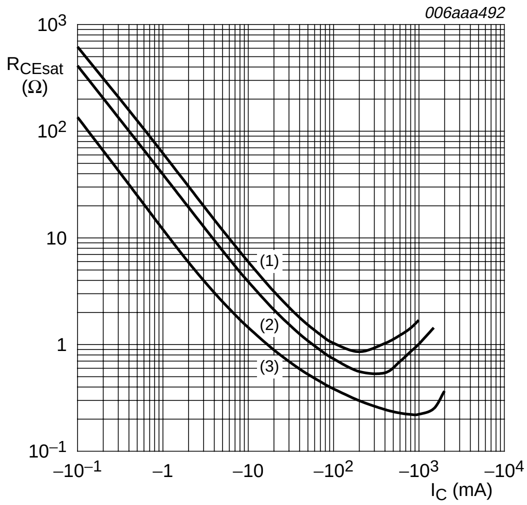
(3) $T_{amb} = -55\ °C$

Fig 10. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\ °C$

Fig 11. Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\ °C$

(1) $I_C/I_B = 100$

(2) $I_C/I_B = 50$

(3) $I_C/I_B = 10$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

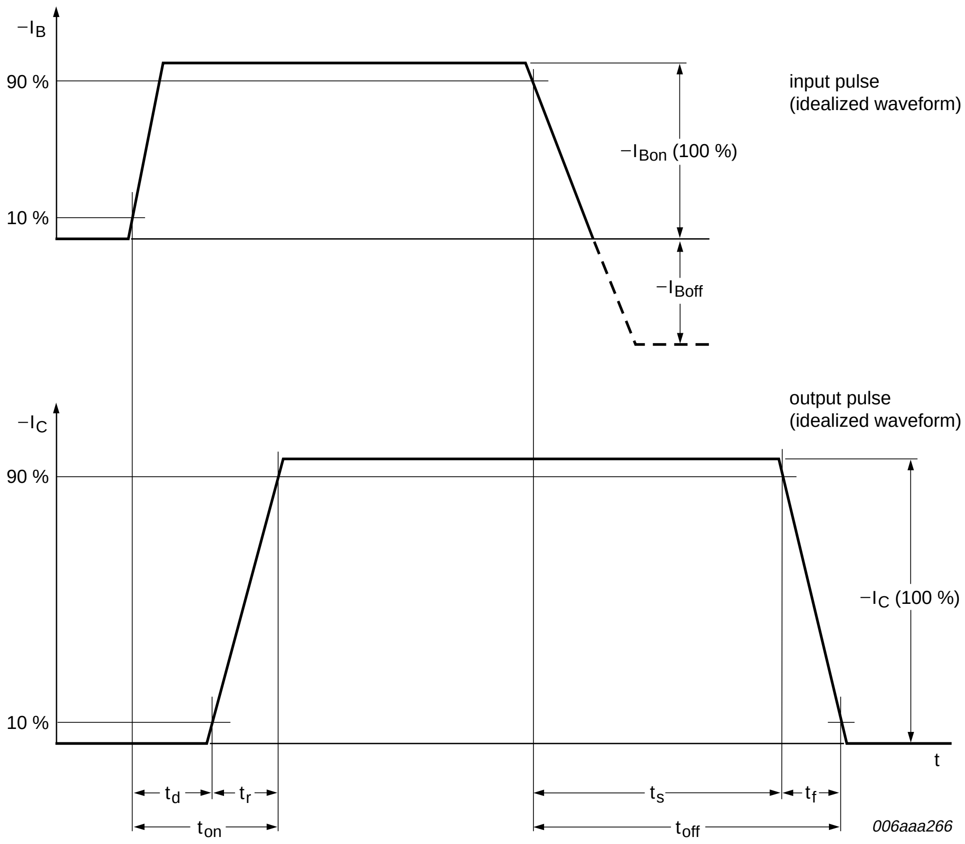
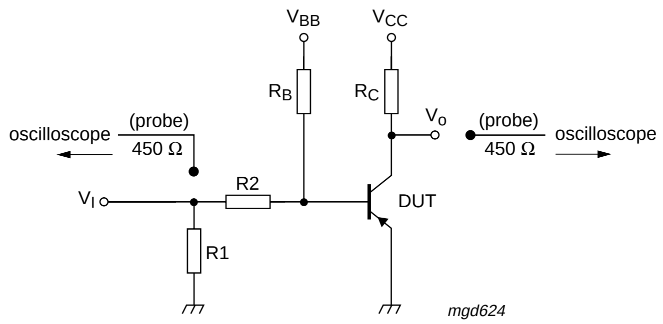


Fig 13. BISS transistor switching time definition



I_C = –0.5 A; I_{Bon} = –25 mA; I_{Boff} = 25 mA; R1 = open; R2 = 100 Ω; R_B = 300 Ω; R_C = 20 Ω

Fig 14. Test circuit for switching times

9. Package outline

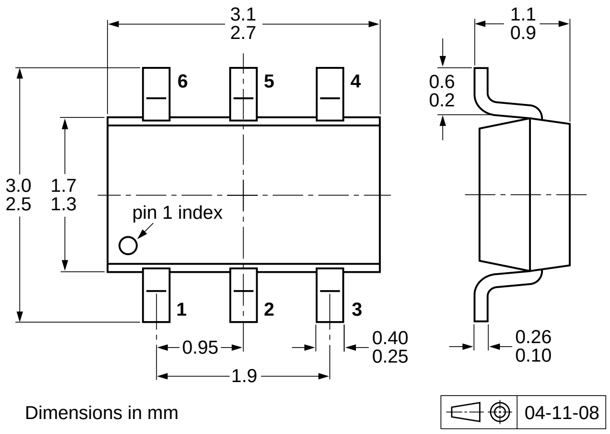


Fig 15. Package outline SOT457 (SC-74)

10. Packing information

Table 8: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

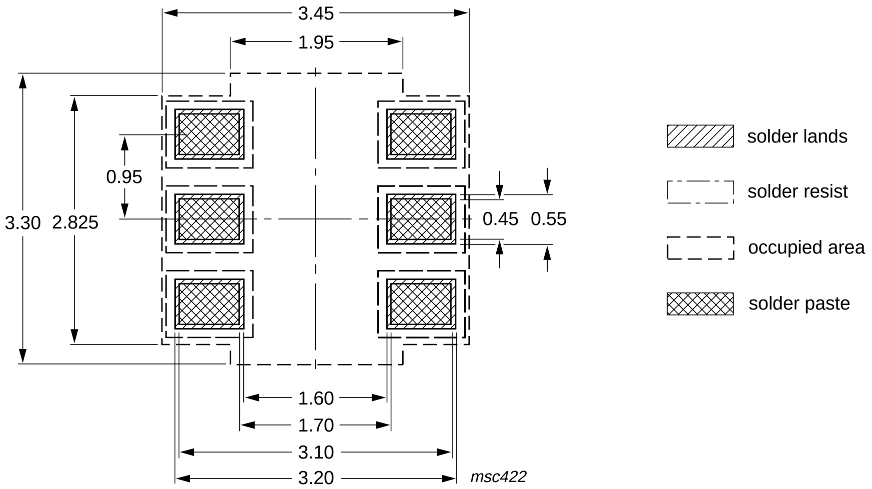
Type number	Package	Description		Packing quantity	
				3000	10000
PBSS5160DS	SOT457	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

[1] For further information and the availability of packing methods, see Section 17.

[2] T1: normal taping

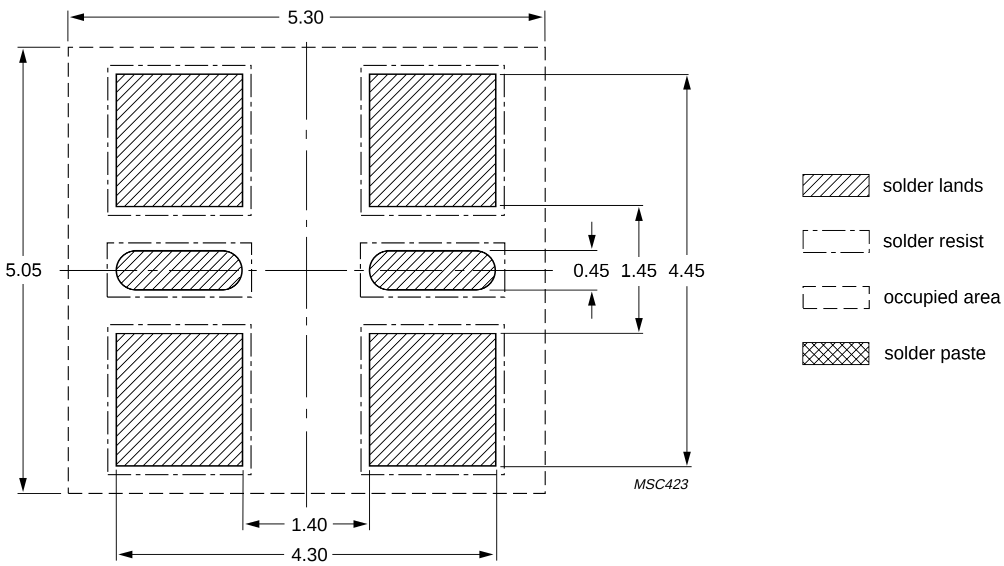
[3] T2: reverse taping

11. Soldering



Dimensions in mm

Fig 16. Reflow soldering footprint



Dimensions in mm

Fig 17. Wave soldering footprint

12. Revision history

Table 9: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PBSS5160DS_2	20050628	Product data sheet	-	9397 750 15186	PBSS5160DS_1
Modifications:	• Product status changed • Table 7: Switching time parameters t_d, t_r, t_{on}, t_s, t_f and t_{off} added • Figure 13 “BISS transistor switching time definition”: added • Figure 14 “Test circuit for switching times”: added • Section 10 “Packing information”: added • Section 11 “Soldering”: added • Section 16 “Trademarks”: added				
PBSS5160DS_1	20040716	Objective data sheet	-	9397 750 12704	-

13. Data sheet status

Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

14. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

15. Disclaimers

Life support — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status ‘Production’), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

16. Trademarks

Notice — All referenced brands, product names, service names and trademarks are the property of their respective owners.

17. Contact information

For additional information, please visit: **http://www.semiconductors.philips.com**

For sales office addresses, send an email to: **sales.addresses@www.semiconductors.philips.com**

18. Contents

1 **Product profile** 1
1.1 General description. 1
1.2 Features 1
1.3 Applications 1
1.4 Quick reference data. 1
2 **Pinning information** 2
3 **Ordering information** 2
4 **Marking** 2
5 **Limiting values** 2
6 **Thermal characteristics** 4
7 **Characteristics** 6
8 **Test information** 9
9 **Package outline** 10
10 **Packing information** 10
11 **Soldering** 11
12 **Revision history** 12
13 **Data sheet status** 13
14 **Definitions** 13
15 **Disclaimers** 13
16 **Trademarks** 13
17 **Contact information** 13

Date of release: 28 June 2005
Document number: 9397 750 15186

Published in The Netherlands